Please amend the specification as follows:

Please amend the title on page 1 and the abstract page as follows:

~~INTERFACIAL STRENGTHENING FOR~~ ELECTROLESS NICKEL IMMERSION GOLD ~~SUBSTRATES~~ SEMICONDUCTOR FLIP CHIP PACKAGE

Please amend the first paragraph of page 1 as follows:

This application is a continuation of U.S. Patent Application No. 10/382,784 filed March 5, 2003, titled INTERFACIAL STRENGTHENING FOR ELECTROLESS NICKEL IMMERSION GOLD SUBSTRATES (now U.S. Patent No. 6,756,687, issued June 29, 2004), which is incorporated herein by reference in its entirety and for all purposes.

Please amend the paragraph bridging pages 5 and 6 as follows:

Fig. 1A shows a cross-sectional view of a flip chip package in accordance with one embodiment of the present invention. The package 100 includes a flip chip (die) 102 electrically connected on its active circuit surface to conductive traces on the chip side of an electroless nickel immersion gold packaging substrate 104 by solder bonds 106. The flip chip may be of any type, but is typically a silicon-based composite. In specific embodiments the package includes a high density flip chip, for example, the APEX™ EP20K400EFC672 chip, available from Altera Corporation, San Jose, CA. The solder for the chip to substrate bonds is typically a high Pb solder with a reflow temperature greater than that for the solder used for the BGA so that the chip-substrate solder bond is not compromised during heating to reflow the BGA solder when the package is subsequently connected to a printed circuit board (PCB). For example, a high Pb solder with a reflow temperature of 200°C or more may be used.